East Search						3/26/0
" Search	L No.	Hits	Text Search			Data Bases
			(("257/52,55,58,62,63") or			USPAT; EPO; JPO;
IS&R	L2	1453	("438/48,482")).CCLS.		3/26/01 11:07	Derwent; IBM TDB
						USPAT; EPO; JPO;
BRS	L3	311	2 and polycrystalline		3/26/01 11:07	Derwent; IBM TDB
						USPAT; EPO; JPO;
BRS	L4	92	3 and (ni au co)		3/26/01 11:10	Derwent; IBM TDB
						USPAT; EPO; JPO;
BRS	L5	4	4 and nucleus		3/26/01 11:11	Derwent; IBM TDB
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-				T : 1		

Search Result

USPAT	Date	Page	Title	Cl/Sub	Cl/Sub	Inventor .
COLAT	Date	age	MANUFACTURE OF	C//Sub	The Mountain	TAJIMA, KAZUHIRO ,
JP 02052419 A	19900222	3	SEMICONDUCTOR SUBSTRATE		138/182 - 138/188 -	NOGUCHI, TAKASHI
JI 02032417 A	19900222		Semiconductor device and method for	 	430/402, 430/400,	NOGOCIII, TAKASIII
US 5888857 A	19990330	22		438/162	120/166 . 120/102	Thoma Hanguana et al
US 3000037 A	19990330	23	manufacturing the same	438/102	438/166 ; 438/482 257/347 ; 257/348 ;	Zhang, Hongyong, et al.
İ					257/349; 257/350;	i ·
			•		257/351; 257/352;	
					257/353; 257/50;	
					257/52 ; 257/57 ;	
					257/63 ; 257/64 ;	
			Semiconductor device having a catalyst		257/65 ; 257/67 ;	
US 6084247 A	20000704	40	enhanced crystallized layer	257/58	257/70	Yamazaki, Shunpei, et al.
					257/58; 257/60;	
	- 1			İ	257/61 ; 257/62 ;	
	İ				257/63 ; 257/64 ;	
					257/65 ; 257/66 ;	•
	1				257/67 ; 257/68 ;	
			Semiconductor thin film, semiconductor		257/69 ; 257/70 ;	
	ŀ		device and manufacturing method		257/71 ; 257/72 ;	
US 6093937 A	20000725		thereof	257/59	257/75	Yamazaki, Shunpei, et al.
			,	<u> </u>		
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East Search 3/26/01

Search	L No.	Hits	ilext Search		Data Bases
					USPAT; EPO; JPO;
BRS	Lì	85678	crystallization	3/26/01 11:22	Derwent; IBM TDB
					USPAT; EPO; JPO;
BRS	L2	2957	l and polycrystalline	3/26/01 11:22	/
					USPAT; EPO; JPO;
BRS	L3	1219	2 and (ni au co)	3/26/01 11:23	
				l i	USPAT; EPO; JPO;
BRS	L4	125	3 and nucleus	3/26/01 11:24	Derwent; IBM TDB
					USPAT; EPO; JPO;
BRS	L5	106	4 and amorphous	3/26/01 11:24	Derwent; IBM TDB
	ü				USPAT, EPO, JPO;
BRS	L6	74	5 and low adj temperature	3/26/01 11:27	Derwent; IBM TDB

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USPAT	Datë 🛴	Page	Title	Cl/Sub	Cl/Sub	Inventor
	evenings of \$1		Photosensitive member having a			
			photoconductive layer comprising a			
			carbonic film for use in			
US 4892800 A	19900109	25	electrophotography	430/85	430/95	Sugata, Masao, et al.
					117/8; 257/66;	
1			Method for manufacturing		438/154 ; 438/30 ;	
US 5403772 A	19950404	23	semiconductor device	438/166	438/96 ; 438/97	Zhang, Hongyong, et al.
			Method of manufacturing semiconductor		148/DIG.16;	
			device having different orientations		438/166 ; 438/30 ;	
US 5614426 A	19970325	13	of crystal channel growth	438/150	438/982	Funada, Fumiaki, et al.
			Method for producing semiconductor			
			device with a gate insulating film		438/591 ; 438/762 ;	
US 5620910 A	19970415	23	consisting of silicon oxynitride	438/151	438/771 ; 438/909	Teramoto, Satoshi
			Solar cell and method for fabricating the			
US 5797999 A	19980825	14	same	136/258	438/97	Sannomiya, Hitoshi, et al.
			Semiconductor device and method for		257/347 ; 257/65 ;	
US 5814835 A	19980929	19	fabricating the same	257/64	257/66	Makita, Naoki, et al.
	-		Semiconductor device and method for			
US 5837569 A	19981117			438/166	438/486 ; 438/488	Makita, Naoki, et al.
			Method for forming crystal and crystal		117/105 ; 117/95 ;	
US 5846320 A	19981208	28	article obtained by said method	117/90	427/249.12	Matsuyama, Jinsho, et al.
			Semiconductor device and method for			
US 5851860 A	19981222	29	producing the same	438/166	438/486	Makita, Naoki, et al.
				l	<u> </u>	<u> </u>